

**Amendments to the Claims**

Claims 1-66 (Cancelled).

67. (Previously presented) A composition of matter comprising a compound having the formula  $(\text{CH}_3)_x\text{Si}_3\text{N}_{(4-x)}$ , with x being greater than 0 and no greater than 4.

68. (Previously presented) The composition of claim 67 further comprising  $\text{Si}_3\text{N}_y$ , where y is about 4/3.

69. (Previously presented) The composition of claim 67 wherein x is from about 1 to about 4.

70. (Previously presented) The composition of claim 67 wherein x is about 0.7.

71. (Currently amended) The composition of claim ~~68~~ 67 having a concentration of  $(\text{CH}_3)_x\text{Si}_3\text{N}_{(4-x)}$  of from greater than 0 mole % to about 20 mole %.

72. (Currently amended) A semiconductor barrier layer over a semiconductor substrate, the barrier layer comprising a compound having the formula  $(\text{CH}_3)_x\text{Si}_3\text{N}_{(4-x)}$ , with x being greater than 0 and no greater than 4.

73. (Previously presented) The semiconductor barrier layer of claim 72 further comprising  $\text{Si}_3\text{N}_y$ , where y is about 4/3.

74. (Currently amended) The semiconductor barrier layer of claim ~~73~~ 72 having a concentration of  $(\text{CH}_3)_x\text{Si}_3\text{N}_{(4-x)}$  of from greater than 0 mole % to about 20 mole %, wherein x is from about 1 to about 4.